

TLP3041(S), TLP3042(S), TLP3043(S)

OFFICE MACHINE

HOUSEHOLD USE EQUIPMENT

TRIAC DRIVER

SOLID STATE RELAY

The TOSHIBA TLP3041 (S), TLP3042 (S) and TLP3043 (S) consist of a zero voltage crossing turn-on photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

All parameters are tested to the specification of TLP3041, TLP3042, TLP3043.

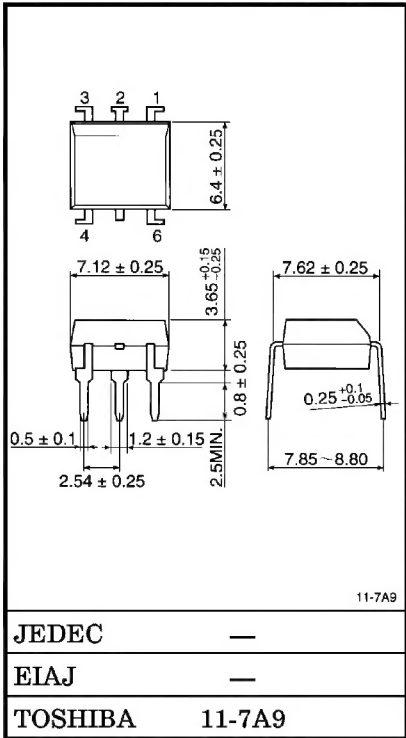
- Peak Off-State Voltage : 400V (Min.)
- Trigger LED Current : 15mA (Max.) (TLP3041)
10mA (Max.) (TLP3042)
5mA (Max.) (TLP3043)
- On-State Current : 100mA (Max.)
- UL Recognized : UL1577, File No. E67349
- Isolation Voltage : 5000V_{rms} (Min.)
- Option (D4) Type
- VDE Approved : DIN VDE0884 / 06.92
Certificate No. 68329
- Maximum Operating Insulation Voltage : 890V_{PK}
- Highest Permissible Over Voltage : 8000V_{PK}

(Note) When a VDE0884 approved type is needed, please designate the “Option (D4)”

● Device Construction

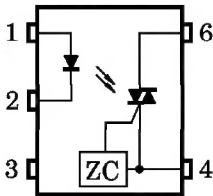
	7.62mm pich standard type	10.16mm pich (LF2) type
Creepage Distance	7.0mm (Min.)	8.0mm (Min.)
Clearance	7.0mm (Min.)	8.0mm (Min.)
Insulation Thickness	0.5mm (Min.)	0.5mm (Min.)

Unit in mm



Weight : 0.39g

PIN CONFIGURATION (Top view)



980910EBC2

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- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I_F	50	mA
	Forward Current Derating (Ta ≥ 53°C)	$\Delta I_F / ^\circ\text{C}$	-0.7	mA / °C
	Peak Forward Current (100μs pulse, 100pps)	I_{FP}	1	A
	Power Dissipation	P_D	100	mW
	Power Dissipation Derating (Ta ≥ 25°C)	$\Delta P_D / ^\circ\text{C}$	-1.0	mW / °C
	Reverse Voltage	V_R	5	V
	Junction Temperature	T_j	125	°C
DETECTOR	Off-State Output Terminal Voltage	V_{DRM}	400	V
	On-State RMS Current	I_T (RMS)	Ta = 25°C 100	mA
			Ta = 70°C 50	
	On-State Current Derating (Ta ≥ 25°C)	$\Delta I_T / ^\circ\text{C}$	-1.1	mA / °C
	Peak On-State Current (100μs pulse, 120pps)	I_{TP}	2	A
	Peak Nonrepetitive Surge Current (Pw = 10ms, DC = 10%)	I_{TSM}	1.2	A
	Power Dissipation	P_D	300	mW
	Power Dissipation Derating (Ta ≥ 25°C)	$\Delta P_D / ^\circ\text{C}$	-4.0	mW / °C
	Junction Temperature	T_j	115	°C
	Storage Temperature Range	T_{stg}	-55~150	°C
Operating Temperature Range		T_{opr}	-40~100	°C
Lead Soldering Temperature (10s)		T_{sol}	260	°C
Total Package Power Dissipation		P_T	330	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C)		$\Delta P_T / ^\circ\text{C}$	-4.4	mW / °C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%) (Note 1)		BV_S	5000	Vrms

(Note 1) Device considered a two terminal device : Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{AC}	—	—	120	Vac
Forward Current	I_F^*	15	20	25	mA
Peak On-State Current	I_{TP}	—	—	1	A
Operating Temperature	T_{opr}	-25	—	85	°C

※ In the case of TLP3042

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	10	—	pF
DETECTOR	Peak Off-State Current	I_{DRM}	$V_{\text{DRM}} = 400\text{V}$	—	10	100	nA
	Peak On-State Voltage	V_{TM}	$I_{\text{TM}} = 100\text{mA}$	—	1.7	3.0	V
	Holding Current	I_H	—	—	0.6	—	mA
	Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{\text{in}} = 120\text{Vrms}, T_a = 85^\circ\text{C}$ (Fig.1)	200	500	—	$\text{V} / \mu\text{s}$
	Critical Rate of Rise of Commutating Voltage	$dv/dt (c)$	$V_{\text{in}} = 30\text{Vrms}, I_T = 15\text{mA}$ (Fig.1)	—	0.2	—	$\text{V} / \mu\text{s}$

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	TLP3041	I_{FT}	$V_T = 3\text{V}$	—	—	15	mA
	TLP3042			—	5	10	
	TLP3043			—	—	5	
Inhibit Voltage		V_{IH}	$I_F = \text{Rated } I_{\text{FT}}$	—	—	40	V
Leakage in Inhibited State		I_{IH}	$I_F = \text{Rated } I_{\text{FT}}$ $V_T = \text{Rated } V_{\text{DRM}}$	—	100	300	μA
Capacitance Input to Output		C_S	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance		R_S	$V_S = 500\text{V} (\text{R.H.} \leq 60\%)$	5×10^{10}	10^{14}	—	Ω
Isolation Voltage		BV_S	AC, 1 minute	5000	—	—	Vrms
			AC, 1 second (in oil)	—	10000	—	
			DC, 1 minute (in oil)	—	10000	—	Vdc

Fig.1 dv/dt TEST CIRCUIT

